

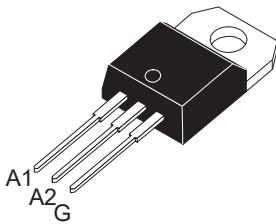
1. Description

NPNN five-layer structure of silicon bidirectional devices; with independent intellectual property rights of single-sided digging technology, table glass passivation process; multi-layer metallized electrodes on the back; with high blocking voltage and high temperature stability.

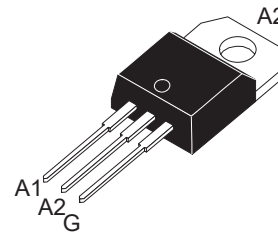
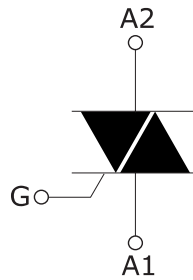
2. Features

vacuum cleaners, power tools and other motor speed controllers; solid state relays; heating controllers (temperature regulation); other phase control circuits.

3. Pinning Information



**TO-220AB
insulated
BTA16**



**TO-220AB
BTB16**



4. Absolute maximum ratings ($T_J=25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Values	Units	
RMS on-state current (full sine wave)	BTA	$I_{T(RMS)}$	16	A	
	BTB				
Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C)	F=50HZ, $t_p=20\text{ms}$		I_{TSM}	160	A
$I^2 t$ value for fusing	$t_p=10\text{ms}$		$I^2 t$	144	A^2S
Critical rate of rise of on-state current $I_G=2 \times I_{GT}$, $t_r \leq 100\text{ns}$	$T_J=125$		di/dt	50	A/us
Off state repetitive peak voltage Reverse repetitive peak voltage	$T_J=25^\circ\text{C}$		V_{DRM}/V_{RRM}	600/800	V
Peak gate current	$t_p=20\mu\text{s}$	$T_J=150^\circ\text{C}$	I_{GM}	4	A
Average gate power dissipation	$T_J=150^\circ\text{C}$		$P_{G(AV)}$	1	W
Storage junction temperature range			T_{STG}	-40 to 150	$^\circ\text{C}$
Operating junction temperature range			T_J	-40 to 150	$^\circ\text{C}$



5.1 Electrical characteristics (3 quadrants)

Parameter	Quadrant	Range	Symbol	Values			Units
				SW	CW	BW	
$V_D=12V$ $R_L=33\Omega$	I	MAX	I_{GT}	SW	CW	BW	mA
		MAX		10	35	50	mA
$V_D=V_{DRM}$, $R_L=3.3k\Omega$, $T_J=125^\circ C$	II	MAX	V_{GT}	1.5			V
	III	MIN	V_{GD}	0.2			V
$I_T=100mA$		MAX	I_H	60			mA
$I_G=1.2 \times I_{GT}$		MAX	I_L	I - III		60	mA
		MAX		II		100	mA
$V_D = 67\% V_{DRM}$, gate open, mA, $T_J=125^\circ C$		MIN	dv/dt	500			V/us
Critical rise rate of commutation voltage $T_J=150^\circ C$		MIN	(dv/dt)c	10			V/us

5.2 Electrical characteristics (4 quadrants)

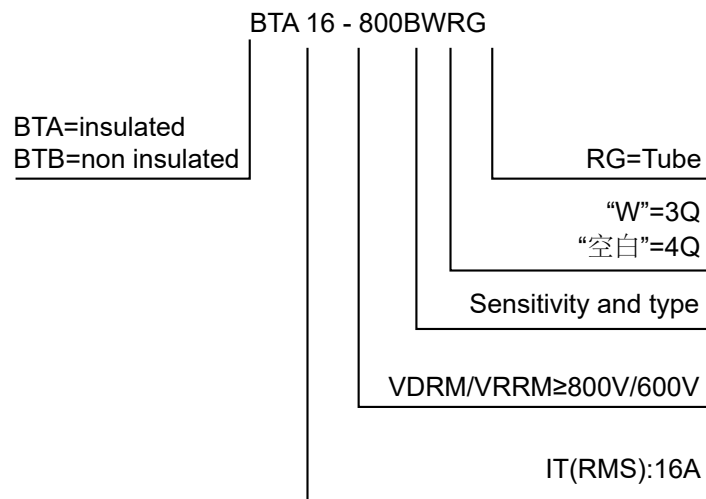
Parameter	Quadrant	Range	Symbol	value				Units
				I	II	III	IV	
$V_D=12V$ $R_L=33\Omega$	I - II - III	MAX	I_{GT}	I	II	III	IV	mA
		MAX		≤ 25	≤ 35	≤ 35	≤ 120	mA
$V_D=V_{DRM}$, $R_L=3.3k\Omega$, $T_J=125^\circ C$	IV	MAX	V_{GT}	1.5				V
		MIN	V_{GD}	0.2				V
$I_T=500mA$		MAX	I_H	60				mA
$I_G=1.2 \times I_{GT}$		MAX	I_L	60				mA
		MAX		100				mA
$V_D = 67\% V_{DRM}$, gate open, mA, $T_J=125^\circ C$		MIN	dv/dt	500				V/us
Critical rise rate of commutation voltage $T_J=150^\circ C$		MIN	(dv/dt)c	10				V/us



6.Static Parameters

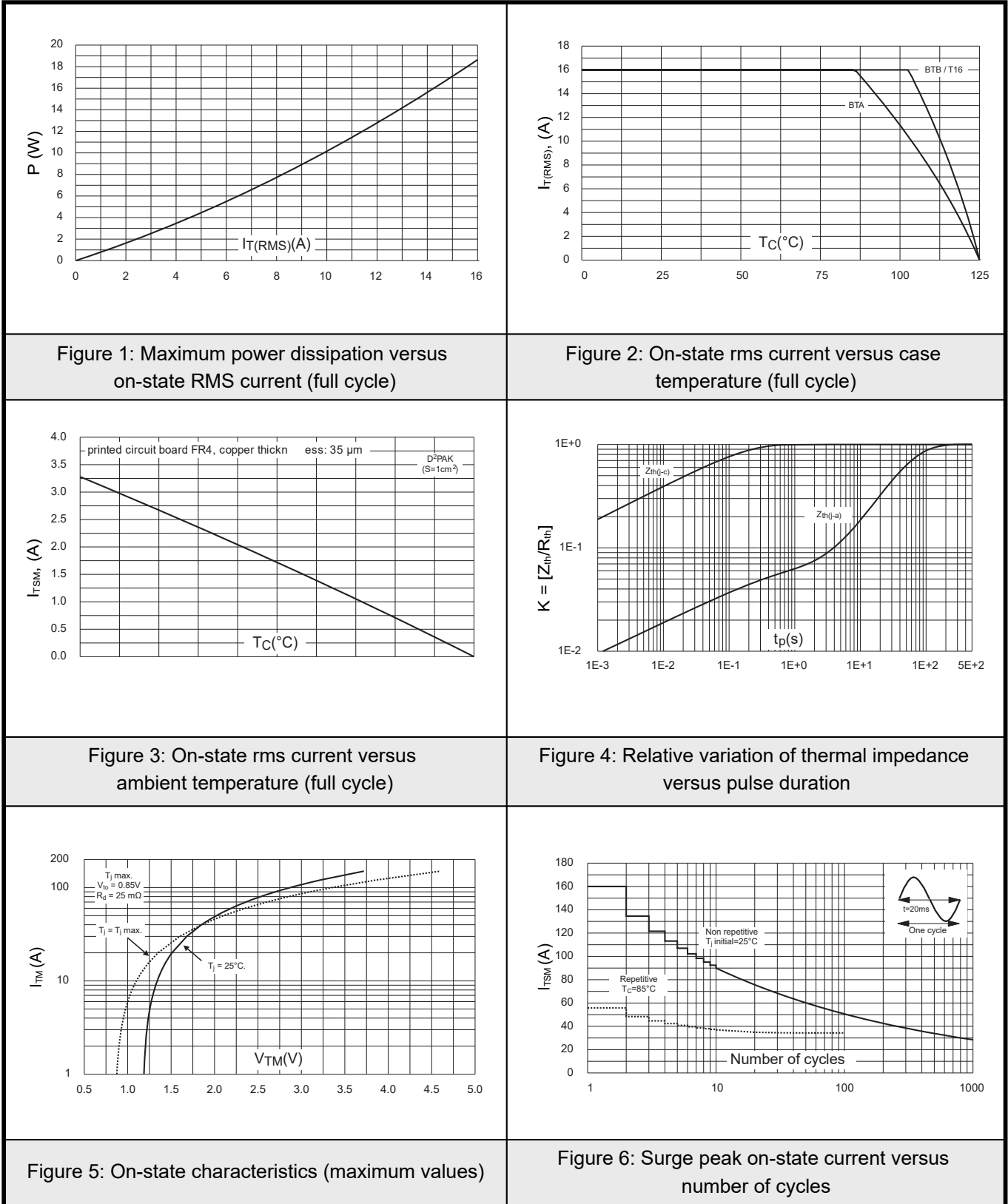
Parameter			Symbol	Values	Units
$I_{TM}=32A$	$T_J=25^{\circ}C$	MAX	V_{TM}	1.5	V
threshold on-state voltage	$T_J=150^{\circ}C$	MAX	V_{T0}	0.87	V
Dynamic resistance	$T_J=150^{\circ}C$	MAX	Rd	14.6	mΩ
$V_{DRM}=V_{RRM}$	$T_J=25^{\circ}C$	MAX	I_{DRM}, I_{RRM}	5	uA
	$T_J=125^{\circ}C$	MAX		1	mA
Junction to ambient	BTA	MAX	$R_{th(j-c)}$	2.1	$^{\circ}C/W$
	BTB	MAX		1.3	$^{\circ}C/W$

7.Static Parameters





8.1 Typical Characteristic





8.2 Typical Characteristic

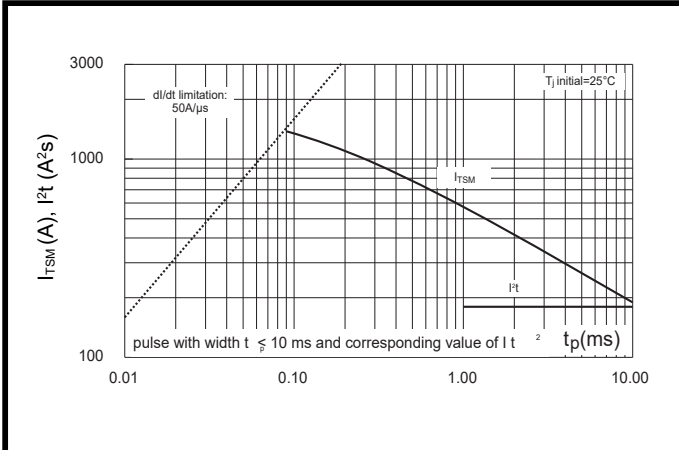


Figure 7: Non-repetitive surge peak on-state current for a sinusoidal

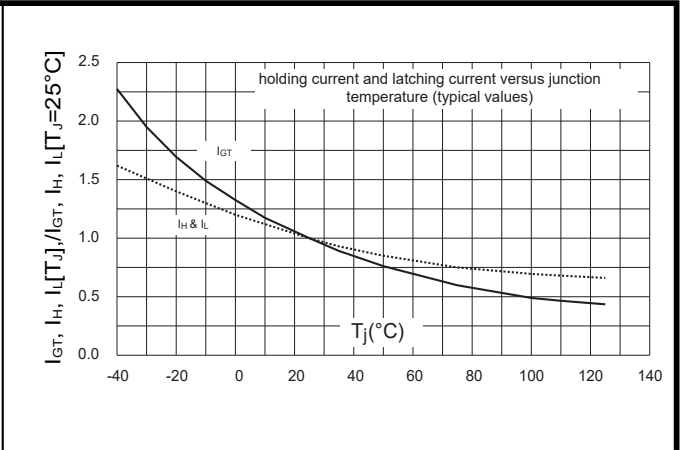


Figure 8: Relative variation of gate trigger current

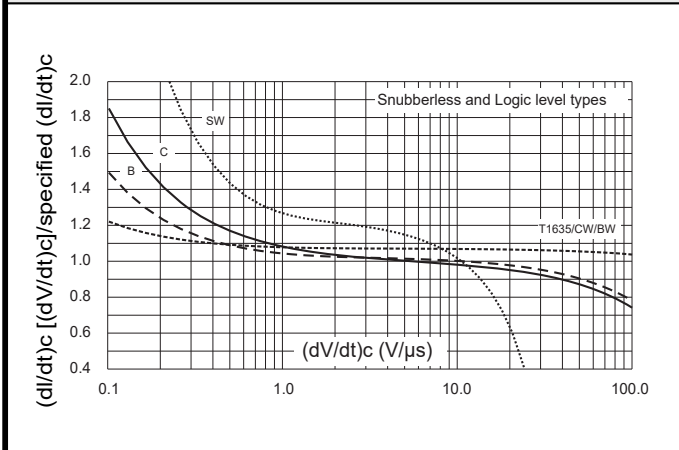


Figure 9: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values)

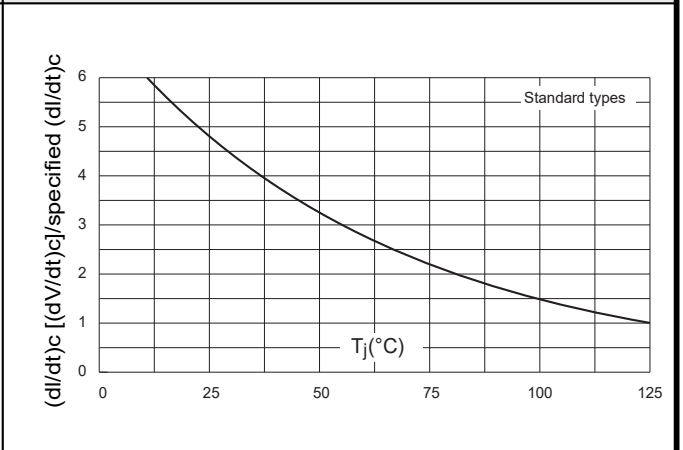


Figure 10: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values)

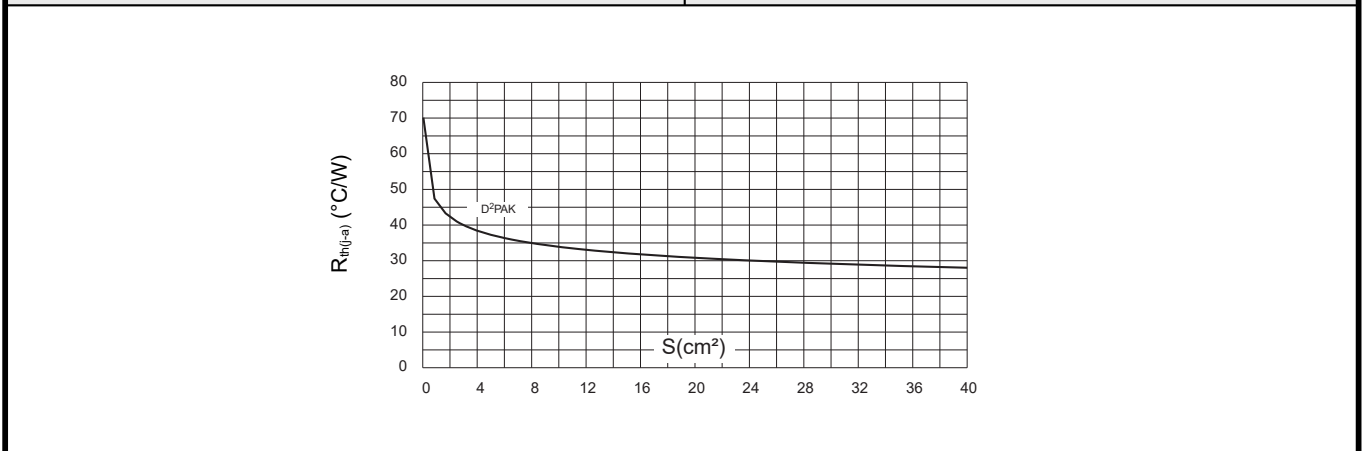
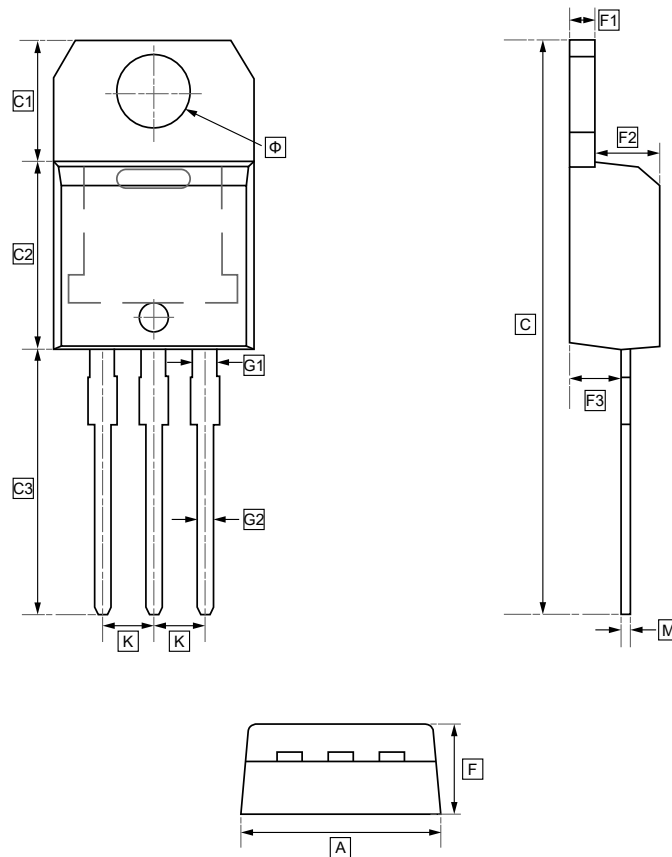


Figure 11: D²PAK thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: 35 μm)



9.TO-220A/B Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	C	C1	C2	C3	Φ	F	F1	F2	F3	G1	G2
Min	9.900	28.600	6.100	9.240	13.160	3.700	4.320	1.200	3.120	2.300	1.200	0.750
Max	10.100	29.000	6.200	9.440	13.460	3.800	4.620	1.300	3.320	2.700	1.300	0.850

Symbol	M	K
Min	0.400	2.540
Max	0.500	



10. Ordering information

BTA16-600BW
UMW yyww

yy: Year Code
 ww: Week Code

Order Code	Marking	Package	Base QTY	Delivery Mode
UMW BTA16-600BRG	BTA16-600B	TO-220A	1000	Tube and box
UMW BTA16-600CRG	BTA16-600C	TO-220A	1000	Tube and box
UMW BTA16-800BRG	BTA16-800B	TO-220A	1000	Tube and box
UMW BTA16-600BWRG	BTA16-600BW	TO-220A	1000	Tube and box
UMW BTA16-600CWRG	BTA16-600CW	TO-220A	1000	Tube and box
UMW BTA16-800BWRG	BTA16-800BW	TO-220A	1000	Tube and box
UMW BTA16-800CWRG	BTA16-800CW	TO-220A	1000	Tube and box
UMW BTA16-600SWRG	BTA16-600SW	TO-220A	1000	Tube and box
UMW BTA16-800SWRG	BTA16-800SW	TO-220A	1000	Tube and box
UMW BTB16-600BRG	BTB16-600B	TO-220B	1000	Tube and box
UMW BTB16-600CRG	BTB16-600C	TO-220B	1000	Tube and box
UMW BTB16-800BRG	BTB16-800B	TO-220B	1000	Tube and box
UMW BTB16-600SWRG	BTB16-600SW	TO-220B	1000	Tube and box
UMW BTB16-600CWRG	BTB16-600CW	TO-220B	1000	Tube and box
UMW BTB16-600BWRG	BTB16-600BW	TO-220B	1000	Tube and box
UMW BTB16-800CWRG	BTB16-800CW	TO-220B	1000	Tube and box
UMW BTB16-800BWRG	BTB16-800BW	TO-220B	1000	Tube and box



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